

(19) World Intellectual Property Organization
International Bureau



(43) International Publication Date
13 September 2001 (13.09.2001)

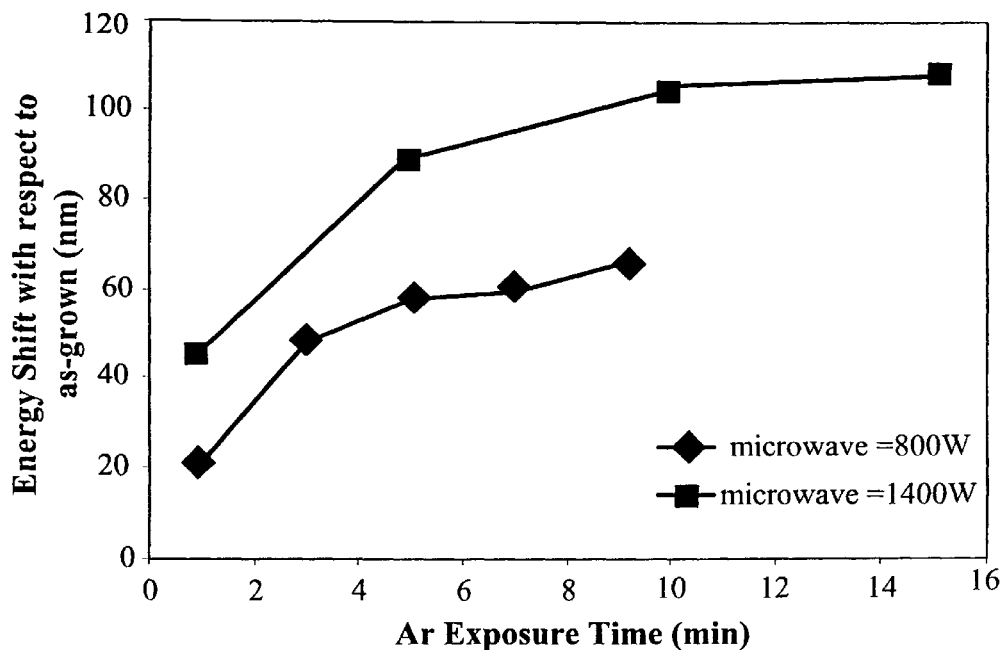
PCT

(10) International Publication Number
WO 01/67568 A1

- (51) International Patent Classification⁷: **H01S 5/026**,
H01L 21/18, 21/266
- (21) International Application Number: PCT/GB01/00898
- (22) International Filing Date: 2 March 2001 (02.03.2001)
- (25) Filing Language: English
- (26) Publication Language: English
- (30) Priority Data:
PCT/SG00/00038 8 March 2000 (08.03.2000) SG
PCT/SG00/00039 8 March 2000 (08.03.2000) SG
2000 04787-8 11 September 2000 (11.09.2000) SG
2000 04786-0 11 September 2000 (11.09.2000) SG
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- (81) Designated States (national): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TR, TT, TZ, UA, UG, US, UZ, VN, YU, ZA, ZW.

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(54) Title: QUANTUM WELL INTERMIXING



(57) Abstract: In a method of manufacturing a photonic integrated circuit having a compound semiconductor structure having a quantum well region, the structure is irradiated using a source of photons to generate defects, the photons having energy (E) at least that of the displacement energy (E_D) of at least one element of the compound semiconductor. The structure is subsequently annealed to promote quantum well intermixing. The preferred radiation source is a plasma generated using an electron cyclotron resonance (ECR) system. The structure can be masked in a differential manner to selectively intermix the structure in a spatially controlled manner by controlling the exposure portions of the structure to the source of radiation.



(84) Designated States (regional): ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GW, ML, MR, NE, SN, TD, TG).

Published:

— with international search report

— before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments

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